TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK2825

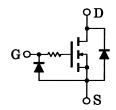
For Portable Equipment
High Speed Switch Applications
Analog Switch Applications

- High input impedance
- 1.5 V gate drive
- Low gate threshold voltage:  $V_{th} = 0.5 \sim 1.0 \text{ V}$
- Small package

### Marking

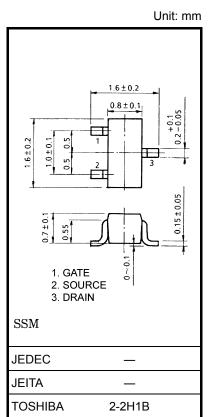
#### **Equivalent Circuit**





#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DS}$	20	V
Gate-source voltage	$V_{GSS}$	10	٧
DC drain current	I <sub>D</sub>	100	mA
Drain power dissipation	$P_{D}$	100	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Weight: 2.4 mg (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: This transistor is electrostatic sensitive device.

Please handle with caution.

# **Electrical Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0	_	_	1	μА
Drain-source breakdown voltage		V <sub>(BR) DSS</sub>	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0	_	_	1	μА
Gate threshold vo	oltage	V <sub>th</sub>	V <sub>DS</sub> = 1.5 V, I <sub>D</sub> = 0.1 mA	0.5	_	1.0	V
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 1.5 V, I <sub>D</sub> = 10 mA	35	70	_	mS
Drain-source ON resistance 1		R <sub>DS</sub> (ON) 1	$I_D = 1 \text{ mA}, V_{GS} = 1.2 \text{ V}$	_	15	50	Ω
Drain-source ON resistance 2		R <sub>DS</sub> (ON) 2	$I_D = 10 \text{ mA}, V_{GS} = 1.5 \text{ V}$	_	10	40	Ω
Drain-source ON	resistance 3	R <sub>DS</sub> (ON) 3	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	7	28	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 1.5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	12	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 1.5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.4	_	pF
Output capacitance		Coss	V <sub>DS</sub> = 1.5 V, V <sub>GS</sub> = 0, f = 1 MHz	_	12	_	pF
Switching time	Turn-on time	t <sub>on</sub>	V <sub>DD</sub> = 1.5 V, I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0~1.5 V	_	0.35	_	0
	Turn-off time	t <sub>off</sub>		_	0.2	_	μS

(2)

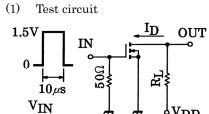
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 $V_{IN}$ 

 $V_{GS}$ 

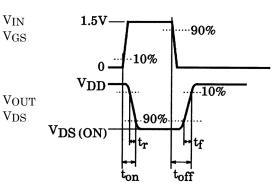
 $V_{\rm DS}$ 

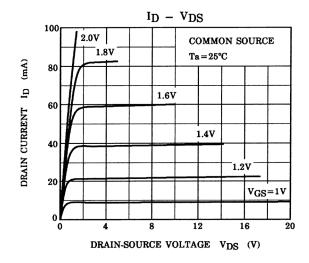
## **Switching Time Test Circuit**

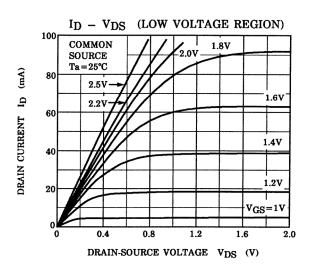


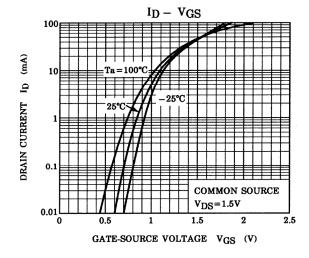
 $\begin{array}{c} OUT & V_{DD} = 1.5V \\ \hline O.U. \leq 1\% \end{array}$  $V_{IN}: t_r, t_f < 5ns$   $(Z_{out} = 50\Omega)$ COMMON SOURCE (3)

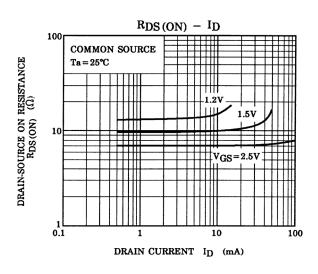
 $Ta = 25^{\circ}C$ 

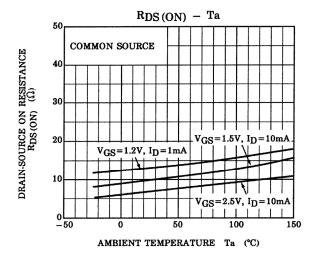


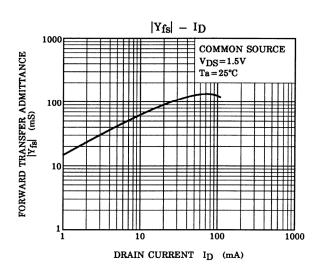


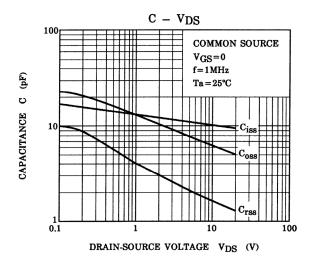


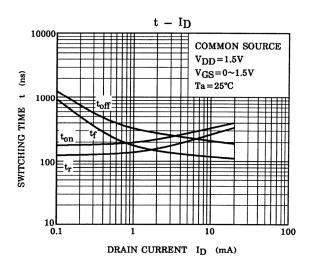


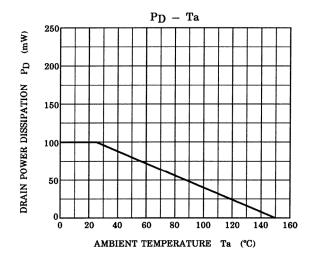












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20070701-EN GENERAL

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